Circuit for clamping bridge overvoltages in voltage-fed quasi-Z-source converter

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Unlike the voltage source converter, the Z-source converter can boost as well as buck the input voltage. However, the presence of physically large components in the impedance network introduces large parasitic inductances into power device commutation paths. This leads to consequent overvoltages at power device turn-off. A simple circuit for addressing this is presented. Practical results are given for a voltage-fed quasi-Z-source inverter with discontinuous input current.

Introduction: Unlike the traditional voltage source converter, the Z-source converter [1] can boost, as well as buck, the input voltage. This can be useful in automotive [2] and renewable energy [3] applications. Fig. 1 shows a voltage-fed quasi-Z-source inverter with discontinuous input current (or ‘Series’ Z-source inverter) [4].

Fig. 1 Voltage-fed quasi-Z-source inverter with discontinuous input current

Device turn-off: At device turn-off, it is desirable that the self-inductance of the loop highlighted in Fig. 2 is minimised. If it is not, a high turn-off voltage occurs at point ‘X’ at the bridge voltage potential, \( v_{bs} \), as the current flowing into that node is commutated. However, because of the likely large volume of the passive components, minimising stray inductances is difficult. Although stray inductance in series with \( L_1 \) and \( L_2 \) is not in itself problematic, the physical size of these components causes the loop area to be large.

Fig. 2 Critical path with loop inductance in quasi-Z-source network

The power switch turn-off action may be made slower to reduce the voltage overshoot, but this increases turn-off losses. Alternatively, snubbers may be used [5]. Fig. 3 shows two variants. A disadvantage of the resistor capacitor diode (RCD) snubber is that its capacitance is charged and discharged once per cycle with losses. The soft clamp snubber does not discharge its capacitance to zero volts and also allows some recovery of energy. However, a difficulty with it in the Z-source converter is that the bridge voltage, \( v_{bs} \), fluctuates continuously between zero and its peak value and as such is not suitable as a soft clamp for DC voltages. Snubber applications in related topologies such as the voltage-fed DC–AC Z-source inverter are addressed in [6, 7], and in a quasi-Z-source DC–DC converter in [8]. This Letter investigates an alternative approach for the Z-source inverter in Fig. 1.

Proposed arrangement: The components in the critical loop are replicated as shown in Fig. 4; referred to as a ‘local replicated network’ (‘LRN’) in this Letter. Auxiliary capacitances \( C_{1\text{aux}} \) and \( C_{2\text{aux}} \) are lower than \( C_1 \) and \( C_2 \) by a factor of 50,000 and \( C_{\text{aux}} \) lower than \( C_{\text{dc}} \) by 30,000; their consequent small physical sizes means the loop is physically smaller. This provides a low-inductance route for current to divert into. Three low-current connections are made to nodes A–C. The absorption of overvoltage peaks charges the auxiliary capacitors. They then discharge directly into their larger equivalent capacitor: \( C_{1\text{aux}} \) discharges into \( C_1 \), and similarly with \( C_{2\text{aux}}/C_2 \) and \( C_{\text{aux}}/C_{\text{dc}} \) respectively. Two or three diodes \( D_{1\text{aux}}/D_{2\text{aux}} \) are connected in series to present a higher aggregate voltage drop across them than \( D_7 \), the main Z-source network diode. Consequently, steady-state current preferentially flows through \( D_7 \) to avoid excess losses in the LRN circuit.

Fig. 3 Conventional snubber networks [5]

Experimental setup: The rig in Fig. 5 is a Z-source inverter (ZSI) corresponding to the circuit in Fig. 1. S1–6 are IKW20N60T co-packaged insulated gate bipolar transistors (IGBTs) and antiparallel diodes. \( D_7 \) is a SCS220AEC silicon carbide Schottky diode. \( L_1 = L_2 = 460 \, \mu \text{H} \). \( C_1 = C_2 = 235 \, \mu \text{F} \) each was formed with film capacitors in parallel. \( C_{\text{dc}} = 140 \, \mu \text{F} \), also being formed with film capacitors in parallel. \( D_7 \) is at a physical distance of \( 166 \, \text{mm} \) from the main bridge components, S1–6. Normally, this is problematic due to a corollary being the introduction of a high parasitic inductance into the loop highlighted in Fig. 2.

Fig. 4 Quasi-Z-source inverter with proposed snubber

The proposed LRN snubber, Fig. 4, was compared with an RCD snubber, Fig. 3. In each case, the converter was operated with a continuous output power of \( 1.5 \, \text{kW} \), an input voltage, \( V_{\text{dc}} \) of 200 V and at a constant shoot-through duty cycle \( (D_{tt}) \) command of 0.1. The bridge IGBTs and diodes (and thereby indirectly the snubbers) were force air cooled. The relevant snubber was fitted physically close to the bridge on the underside of the printed circuit board (PCB). Fig. 6 shows the LRN and RCD snubber components. Details for the LRN snubber are: \( C_{1\text{aux}} = C_{2\text{aux}} = C_{\text{aux}} = 4.7 \, \text{nF} \), 1 kV, ceramic; \( D_{1\text{aux}} = D_{2\text{aux}} = D_{\text{aux}} \), in parallel.

Fig. 5 Experimental quasi-Z-source converter. (Two of capacitors forming \( C_2 \) are mounted on underside of PCB.)

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Optimisation of the LRN snubber component values has not been attempted, but practical measurements have been presented. Further analysis of the snubber operation including a study of energy stored in the stray inductances in the connections made between the LRN components and the nodes A–C in the main impedance network, Fig. 4, forms future work in this area.

Conclusion: A snubber circuit has been presented for the voltage-fed quasi-Z-source inverter with discontinuous input current. The proposed arrangement provides overshoot suppression similar to the conventional RCD snubber, but with the advantages of much lower-power dissipation and without an increase in the peak bridge input voltage associated with RCD snubbers.

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References

Figures

- Fig. 6 Views of snubber components on underside of converter PCB: left: LRN snubber, right: RCD snubber

- Fig. 7 Transient $v_{br1}$ at turn-off: top: RCD snubber, bottom: proposed LRN snubber

- Fig. 8 Thermal images of bridge devices (top) and snubber components: left: RCD snubber, right: LRN snubber